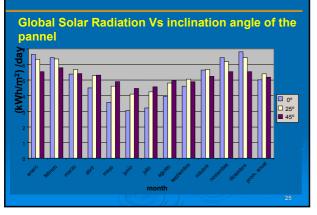
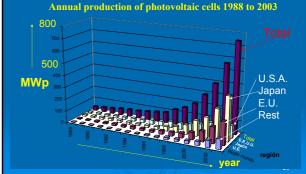
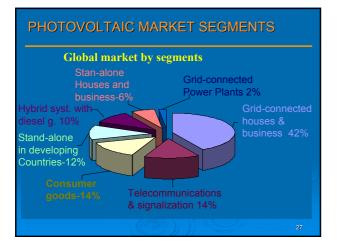
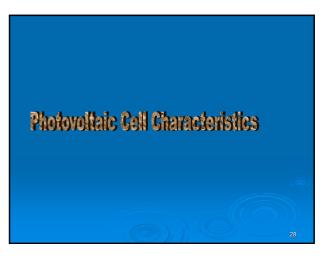
Global Solar Radiation



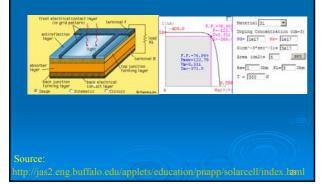
Evolution of Photovoltaic cells production







Solar Cell: Design Calculation



Silicon Cells

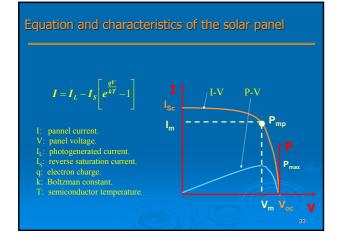
- > Single-Crystalline Silicon: presents a completely ordered structure, whose uniform behavior turns it optimal semiconductor, but of onerous manufacture. Easily reconocible by his dark and metallic bluish monochrome.
- Polycrystalline Silicon: presents ordered structures separated by regions. The irregular connections of the crystalline borders diminish the yield of the cell, limiting the photocurrent generation. Its aspect is a composition of different crystal of metallic bluish and gray color.

Amorphous Silicon Cells

- They differ from the other crystalline structures presenting a high degree of disorder in the structure of the atoms. They contain a great number of structural defects and connections.
- Presenting a spectral response with displacement to the blue, are very efficient under artificial illumination (mainly under fluorescent lamps).
- The efficiency in this case is superior to the crystalline silicon. Amorphous silicon cells have a simpler manufacturing process than crystalline cells and, therefore, a lower cost.

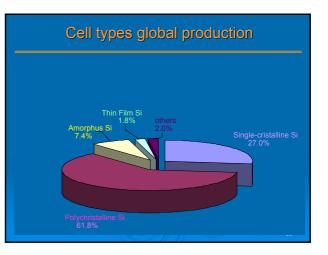
Thin film photovoltaic cells

- > Thin film cells use Copper Indium Diselenide, Cadmium Telluride (CdTe), and Gallium Arsenide as thin film materials, typically a few μm or less in thickness, directly deposited on glass, stainless steel, ceramic or other compatible substrate materials.
- > Thin film technology uses less material per square area of the cell, hence, is less expensive per watt of power generated.

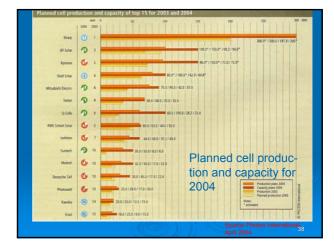


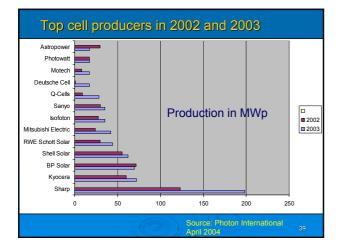
Efficiency of Photovoltaic Cells Silicon cells FF % Test Area Descrip cm² Center Fact Si (crystalline) 24.7 ±0- 4.00 0.706 Sandi UNSW (da) PERL7 а (3/99) Si (multicrystalline) 19-8±0-5 I.09(ap) 0.654 38-1 79.5 Sandi UNSW/ Eurosolare а (2/98) 16-6 ±0.4 0.645 Si (thin film transfer) 32.8 78.2 FhG-University of Stuttgart (ap) ISE(7 |^m thick)8 Source: Martin A. Green e.a.-Progress in Photovolti ch and Application ns 2003-11 Resea

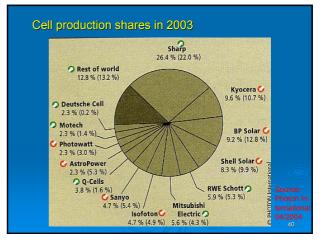
| III-V cells | | | | | | | |
|--------------------------------|----------------|--------------|-------|----------|------|-----------------------------------|-----------------------------|
| GaAs (crystalline) | 25.1 ±0.8 | 3.91 (t) | 1.022 | 28. 2 | 87.1 | NREL (3/90) | Kopin, AlGaAs window |
| GaAs (thin film) | 23.3 ±0.7 | 4.00 (ap) | 1.011 | 27. 6 | 83.8 | NREL (4/90) | Kopin, 5 mm CLEFT9 |
| GaAs (multicrysta Iline) | 18.2 ±0.5 | 4.011 (t) | 0.994 | 23. 0 | 79.7 | NREL (11/95) | RTI, Ge substrate 10 |
| InP (crystalline) | 21.9±0.7 | 4.02 (t) | 0.878 | 29. 3 | 85.4 | NREL (4/90) | Spire, epitaxial' |
| Polycrystalline thin film | | | | | | | |
| CIGS (cell) | 18.4±0.5' ' | 1.04 (ap) | 0.669 | 35. 7 | 77.0 | NREL (2/01) | NREL, CIGS or glass12 |
| CIGS (submodule | 16.6 ±0.4 | 16.0 (ap) | 2.643 | 8.3 5 | 75.1 | FhG-ISE (3/00) and Applicat | University o Uppsala, |

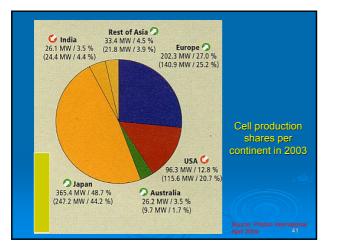


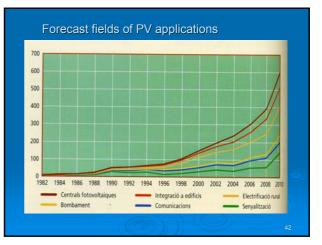














DC/DC Converters for simple applications

Simple charges directly connected

